

One Watt Darlington Transistors

PNP Silicon

• These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

MAXIMUM RATINGS

Rating	Symbol	MPSW63 MPSW64	Unit
Collector - Emitter Voltage	V _{CES}	-30	Vdc
Collector - Base Voltage	V _{CBO}	-30	Vdc
Emitter - Base Voltage	V _{EBO}	-10	Vdc
Collector Current — Continuous	I _C	-500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

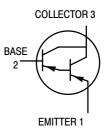
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	50	°C/W

MPSW63 MPSW64*

*ON Semiconductor Preferred Device





ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = -100 \ \mu Adc, \ V_{BE} = 0$)	V _{(BR)CES}	-30	_	Vdc
Collector Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	_	-100	nAdc
Emitter Cutoff Current (V _{EB} = -10 Vdc, I _C = 0)	I _{EBO}	_	-100	nAdc

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

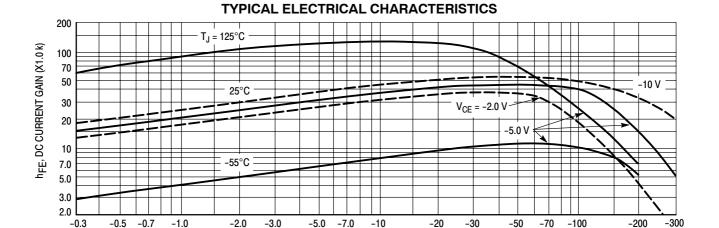
MPSW63 MPSW64

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS ⁽¹⁾		•	•		
DC Current Gain ($I_C = -10 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$)	MPSW63 MPSW64	h _{FE}	5,000 10,000		_
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	MPSW63 MPSW64		10,000 20,000	<u> </u>	
Collector–Emitter Saturation Voltage ($I_C = -100 \text{ mAdc}$, $I_B = -0.1 \text{ mAdc}$)		V _{CE(sat)}	_	-1.5	Vdc
Base–Emitter On Voltage ($I_C = -100 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$)		V _{BE(on)}	_	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ⁽²⁾ (I _C = -10 mAdc, V _{CE} = -5.0 Vdc, f = 100 MHz)		f _T	125	_	MHz

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

^{2.} $f_T = |h_{fe}| \cdot f_{test}$.



I_C, COLLECTOR CURRENT (mA)

Figure 1. DC Current Gain

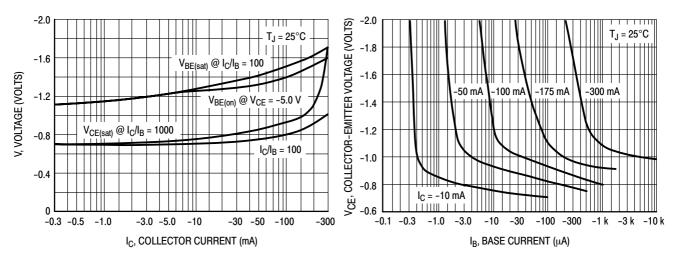


Figure 2. "ON" Voltage

Figure 3. Collector Saturation Region

MPSW63 MPSW64

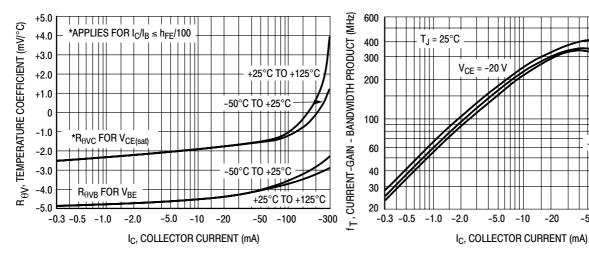


Figure 4. Temperature Coefficients

Figure 5. Current-Gain — Bandwidth Product

-10 V

-50 -100

-5.0 \

-300

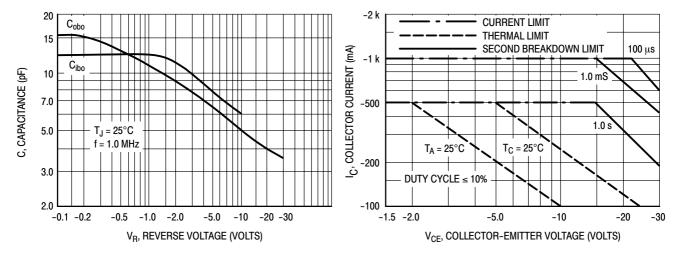


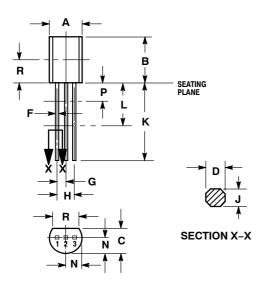
Figure 6. Capacitance

Figure 7. Active Region, Safe Operating Area

MPSW63 MPSW64

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-10 ISSUE ΔI



YLE 1:

PIN 1. EMITTER

2. BASE

3. COLLECTOR

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED
- IS UNCONTROLLED.

 4. DIMENSION F APPULES BETWEEN P AND L
 DIMENSIONS D AND J APPLY BETWEEN L AND K
 MIMIMUM. LEAD DIMENSION IS UNCONTROLLED
 IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.135		3.43	

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